WHAT IS CLAIMED IS:

1. A memory device, comprising:

a memory cell array having variable resistance memory cells that are coupled to and disposed between first conductive lines extending in a first direction and second conductive lines crossing the first conductive lines; and

a selection circuit configured to select the first conductive lines,

wherein the second conductive lines comprise:

straight conductive lines extending in a second direction, the second direction crossing the first direction; and

first bending conductive lines spaced apart from the selection circuit by the straight co nductive lines, the first bending conductive lines extending parallel with each other and havin g an L shape,

wherein each of the first bending conductive lines has a portion extending in the first direction, and

wherein inflection portions of the first bending conductive lines are spaced apart at different distances from each of the first conductive lines.

2. The memory device of claim 1, further comprising:

first contact plugs coupled to the straight conductive lines and extending in a third direction, the third direction being perpendicular to the first direction and the second direction; and

second contact plugs coupled to the first bending conductive lines and extending in the third direction, the second contact plugs having resistance smaller than resistance of the first contact plugs.

3. The memory device of claim 2, wherein a width of each of the second contact plugs in the second direction is greater than a width of each of the first contact plugs in the first direction.

4. The memory device of claim 2, wherein each of the second contact plugs includes a first conductive material and a second conductive material, the first and second conductive materials having different resistivity.

5. The memory device of claim 4, wherein one of the first conductive material and the second conductive material is the same as a material included in each of the first contact plugs.

6. The memory device of claim 2,

wherein the straight conductive lines include first straight conductive lines and second straight conductive lines that are alternately arranged in the first direction,

wherein the first contact plugs are divided into a first group that is coupled to the first straight conductive lines and a second group that is coupled to the second straight conductive lines, and

wherein the memory cell array is disposed between the first group of the first contact plugs and the second group of the first contact plugs.

7. A memory device, comprising:

a memory cell array having variable resistance memory cells that are coupled to and disposed between first conductive lines extending in a first direction and second conductive lines crossing the first conductive lines; and

a selection circuit configured to select the first conductive lines,

wherein the second conductive lines comprise:

straight conductive lines extending in a second direction, the second direction crossing the first direction; and

first bending conductive lines spaced apart from the selection circuit by the straight conductive lines, the first bending conductive lines extending parallel with each other and having an L shape,

wherein the first bending conductive lines include first cell line portions and first contact line portions, the first contact line portions extending from the first cell line portions, respectively,

wherein the first cell line portions extend in the second direction and are arranged to be spaced apart from each other in the first direction, and

wherein the first contact line portions extend in the first direction and are arranged to be spaced apart from each other in the second direction.

8. The memory device of claim 7, wherein a distance between two neighboring ones of the first contact line portions is greater than a distance between two neighboring ones of the first cell line portions and a distance between two neighboring ones of the straight conductive lines.

9. The memory device of claim 7, further comprising:

first contact plugs coupled to the straight conductive lines; and

second contact plugs coupled to the first contact line portions and having resistance smaller than resistance of the first contact plugs.

10. The memory device of claim 1,

wherein the second conductive lines further comprise second bending conductive lines crossing the first conductive lines,

wherein the first bending conductive lines are disposed between the second bending

conductive lines and the straight conductive lines in the first direction,

wherein the second bending conductive lines include second cell line portions that are parallel with the straight conductive lines and second contact line portions that extend from the second cell line portions, respectively, toward the straight conductive lines,

wherein the second cell line portions are arranged to be spaced apart from each other in the first direction, and

wherein the second contact line portions are arranged to be spaced apart from each other in the second direction.

11. The memory device of claim 10, wherein a distance between two neighboring ones of the second contact line portions is greater than a distance between two neighboring ones of the second cell line portions and a distance between two neighboring ones of the straight conductive lines.

12. The memory device of claim 10, further comprising:

first contact plugs coupled to the straight conductive lines; and

second contact plugs coupled to the second contact line portions and having resistance smaller than resistance of the first contact plugs.

13. A memory device, comprising:

a first conductive line including first, second, and third portions sequentially arranged in a first direction;

first variable resistance memory cells coupled to the first portion of the first conductive line and arranged in the first direction;

a second variable resistance memory cell coupled to the second portion of the first conductive line;

a third variable resistance memory cell coupled to the third portion of the first

conductive line; and

second conductive lines coupled to the first, second, and third variable resistance memory cells and crossing the first conductive line,

wherein the second conductive lines comprise:

straight conductive lines coupled to the first variable resistance memory cells, respectively;

a first bending conductive line including a first cell line portion and a first contact line portion, the first cell line portion being coupled to the second variable resistance memory cell and crossing the first conductive line, the first contact line portion extending from the first cell line portion in the first direction; and

a second bending conductive line including a second cell line portion and a second contact line portion, the second cell line portion being coupled to the third variable resistance memory cell and crossing the first conductive line, the second contact line portion extending from the second cell line portion toward the straight conductive lines.

14. The memory device of claim 13, further comprising a selection circuit connected to an end of the first conductive line,

wherein the first portion of the first conductive line is disposed closest to the selection circuit among the first, second, and third portions of the first conductive line.

15. The memory device of claim 13, further comprising:

first contact plugs coupled to the straight conductive lines, respectively; and

second contact plugs coupled to the first contact line portion and the second contact line portion, respectively, and having resistance smaller than resistance of the first contact plugs.

16. The memory device of claim 15, wherein a width of each of the second contact plugs in a second direction crossing the first direction is greater than a width of each of the first

contact plugs in the first direction.

17. The memory device of claim 15, wherein each of the second contact plugs includes a first conductive material and a second conductive material, the first conductive material and the second conductive material having different resistivity.

18. The memory device of claim 17, wherein one of the first conductive material and the second conductive material is the same as a material included in each of the first contact plugs.

19. The memory device of claim 13,

wherein the second contact line portion extends from the second cell line portion toward the straight conductive lines, and

wherein the first contact line portion extends from the first cell line portion in a direction opposite to a direction in which the second contact line portion extends from the second cell line portion.

20. The memory device of claim 13, wherein the first contact line portion and the second contact line portion are spaced apart from each other by the first conductive line.

21. The memory device of claim 20, wherein the straight conductive lines include a first straight conductive line and a second straight conductive line that are alternately disposed with each other in the first direction.

22. The memory device of claim 21, further comprising:

a first group contact plug including a first contact plug coupled to the first straight conductive line and a second contact plug coupled to the first contact line portion; and

a second group contact plug including a third contact plug coupled to the second straight conductive line and a fourth contact plug coupled to the second contact line portion,

wherein the first group contact plug and the second group contact plug are spaced apart from each other by the first conductive line.

23. The memory device of claim 22, wherein each of the second contact plug and the fourth contact plug has resistance smaller than resistance of each of the first contact plug and the third contact plug.